

Please amend the specification as follows:

In the first full paragraph on page 8:

A sixth aspect of the invention is characterized in, in the silicon crystal production step of the silicon wafer production method according to the first aspect of the invention, controlling the oxygen concentration in the silicon crystal to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>.

In the second paragraph on page 8:

A seventh aspect of the invention is characterized in, in the silicon crystal production step of the silicon wafer production method according to the second aspect of the invention, controlling the oxygen concentration in the silicon crystal to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>.

In the second paragraph on page 10:

The sixth and seventh aspects of the invention add a still further technical limitation to the silicon crystal production step in, respectively, the first aspect and second aspect of the invention.

Namely, in the silicon crystal production step, the oxygen concentration in the silicon crystal is controlled to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>.

In the third paragraph on page 10:

By controlling the oxygen concentration in the silicon crystal to a low level of no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup> according to the sixth and seventh aspects of the invention, even if the production conditions region extends into epitaxial defect region  $\beta 1$ , no OSF nuclei in the silicon wafer substrate readily grow into OSFs and appear in the epitaxial growth layer as epitaxial defects. As a result, the conditions for selecting the boron concentration and the growth condition V/G can be relaxed, enabling the yield to be improved even further.

In the second full paragraph on page 11:

A tenth aspect of the invention is characterized in, in the silicon crystal production step of the silicon wafer production method according to the ninth aspect of the invention, controlling the oxygen concentration in the silicon crystal to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>.

In the first full paragraph on page 12:

By controlling the oxygen concentration within the silicon crystal to a low concentration of  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup> or less in accordance with the tenth aspect of the invention, even if the crystal production conditions region extends into the epitaxial defect region  $\beta 1$ , no OSF nuclei in the silicon wafer substrate grow into OSFs and appear as epitaxial defects in the epitaxial growth layer. The conditions for setting the boron concentration and growth condition V/G can thus be relaxed, enabling the production yield to be increased even further.

In the fourth paragraph on page 24:

In this Production Example 6, during production of a silicon crystal 10 in Production Method 1, control of the oxygen concentration in the silicon crystal 10 to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup> is added.

In the sixth paragraph bridging pages 24-25:

Here, control is carried out limiting the oxygen concentration in the silicon crystal 10 to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>. When the silicon crystal 10 has a low oxygen concentration, even if the crystal production conditions region extends into epitaxial defect region  $\beta 1$ , OSF nuclei in the silicon wafer substrate do not readily grow into OSF defects and appear as epitaxial defects in the epitaxial growth layer. This allows the conditions for setting the boron concentration and the growth condition V/G to be relaxed, enabling the production yield to be further enhanced.

In the third full paragraph on page 25:

Oxygen concentration and heat treatment conditions to keep OSF nuclei from developing into OSFs are listed below.

- 1) Controlling the oxygen concentration in the silicon crystal 10 to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>, and administering heat treatment in a dry O<sub>2</sub> gas atmosphere at 1000°C for 16 hours.
- 2) Controlling the oxygen concentration in the silicon crystal 10 to no more than 11 atoms/cm<sup>3</sup>,

and administering heat treatment in a wet O<sub>2</sub> gas atmosphere at 650°C for 3 hours and at 1100°C for 2 hours.

In the third paragraph on page 27:

In this Production Method 9, during production of the silicon crystal 10 by Production Method 8, a control is added so as to limit the oxygen concentration in the silicon crystal 10 to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>.

In the fifth paragraph on page 27:

Hence, control is carried out which limits the oxygen concentration in the silicon crystal 10 to no more than  $12.5 \times 10^{17}$  atoms/cm<sup>3</sup>. By giving the silicon crystal 10 a low oxygen concentration, even if the crystal production conditions region should extend into epitaxial defect region β1, no OSF nuclei in the silicon wafer substrate grow into OSF defects and appear in the epitaxial growth layer as epitaxial defects. The boron concentration and the growth condition V/G setting conditions can thus be relaxed, enabling further improvement in the production yield.